MSI High Speed Low Power GaAs ICs Using Schottky Diode FET Logic (1979 [MWSYM])

S.I. Long, B.M. Welch, R.C. Eden, F.S. Lee and R. Zucca. "MSI High Speed Low Power GaAs ICs Using Schottky Diode FET Logic (1979 [MWSYM])." 1979 MTT-S International Microwave Symposium Digest 79.1 (1979 [MWSYM]): 509-511.

A new approach to the design and fabrication of planar high speed GaAs integrated circuits is described. Experimental digital circuits of MSI level complexities have been fabricated showing high gate density, low dynamic switching energies and very high switching speeds.

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